DACO SEMICONDUCTOR CO., LTD.

MBRQ601100CT(R)

SCHOTTKY DIODE MODULE TYPE 600A

Features

High Surge Capability

Type 100V V_{RRM}

TWIN TOWER Q

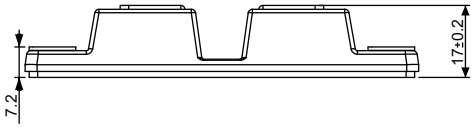
Maximum Ratings

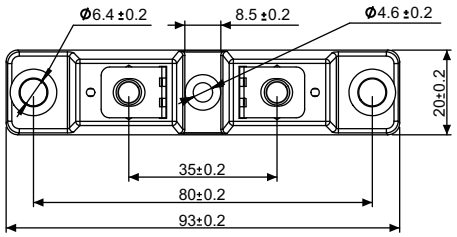
Operating Temperature: -55 ℃ to +150 ℃

Storage Temperature: -55 ℃ to +150 ℃

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRQ601100CT(R)	100V	70V	100V

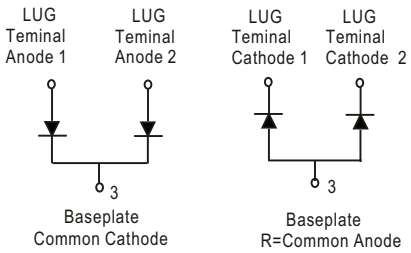
Dimensions in mm (1 mm = 0.0394")





Electrical Characteristics @ 25 ℃ Unless Otherwise Specified

Average Forward Current (Per pkg)	$I_{F(AV)}$	600A	TC=125℃
Peak Forward Surge Current (Per leg)	I_{FSM}	5200A	8.3ms , half sine
Maximum Instantaneous Forward Voltage (Per leg) NOTE (1)	V_F	0.80V	I_{FM}=300A; T_J=25 ℃
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg) NOTE (1)	I_R	1mA 10mA 50mA	TJ = 25 ℃ TJ = 100 ℃ TJ = 150 ℃
Maximum Thermal Resistance Junction To Case (Per leg)	$R_{\theta jc}$	0.13℃/W	
Mounting torque		3 ± 0.5Nm 3 ± 0.5Nm	To heatsink To terminals



NOTE :

(1) Pulse Test: Pulse Width 300 μ sec. Duty Cycle < 2%

Figure.1 - Typical Forward Characteristics

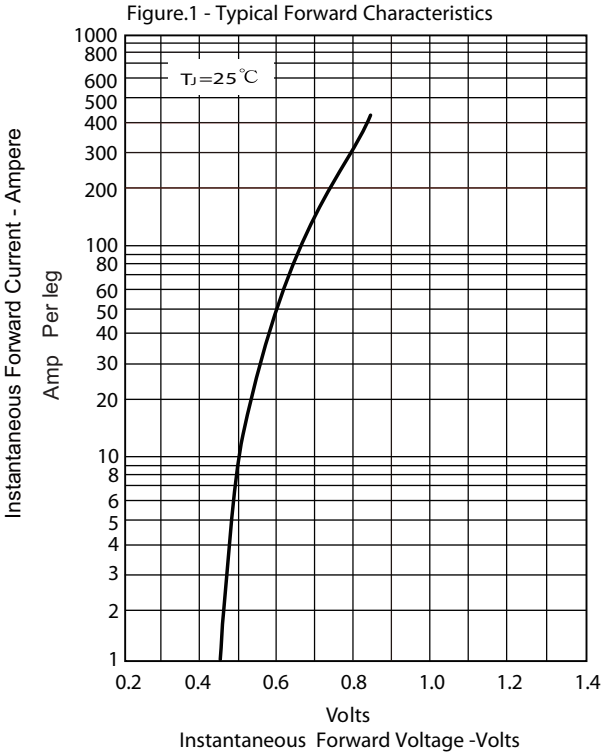
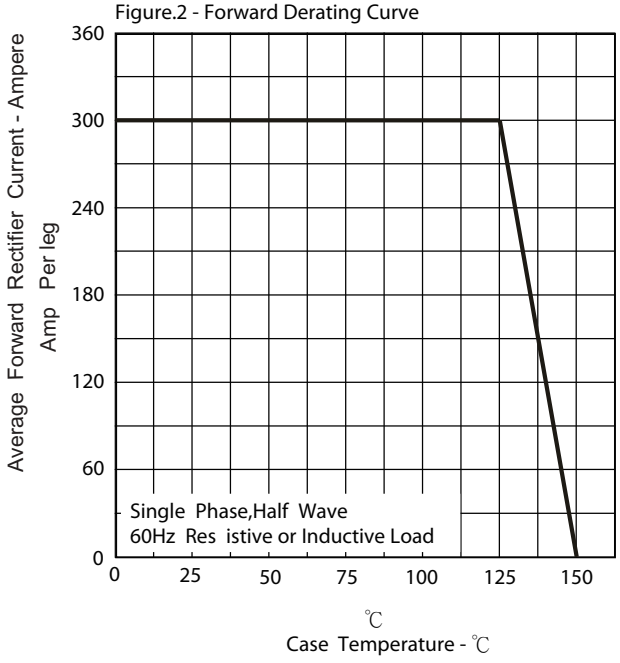


Figure.2 - Forward Derating Curve



Figupre.3 - Peak Forward Surge Current

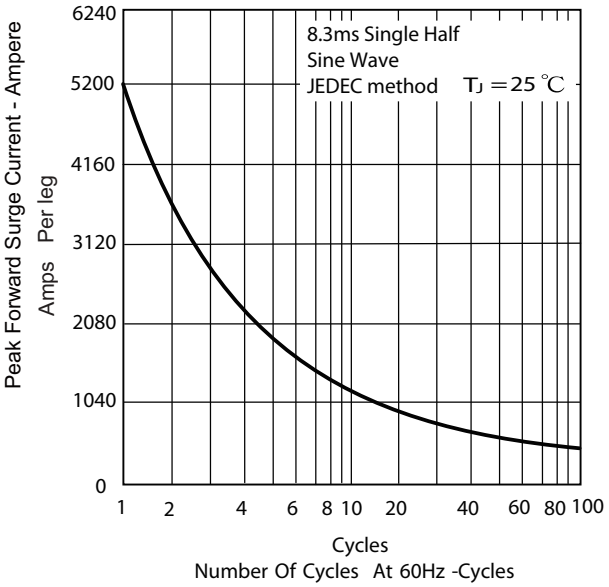


Figure.4 - Typical Reverse Characteristics